

Fig. 1 (Prior Art)

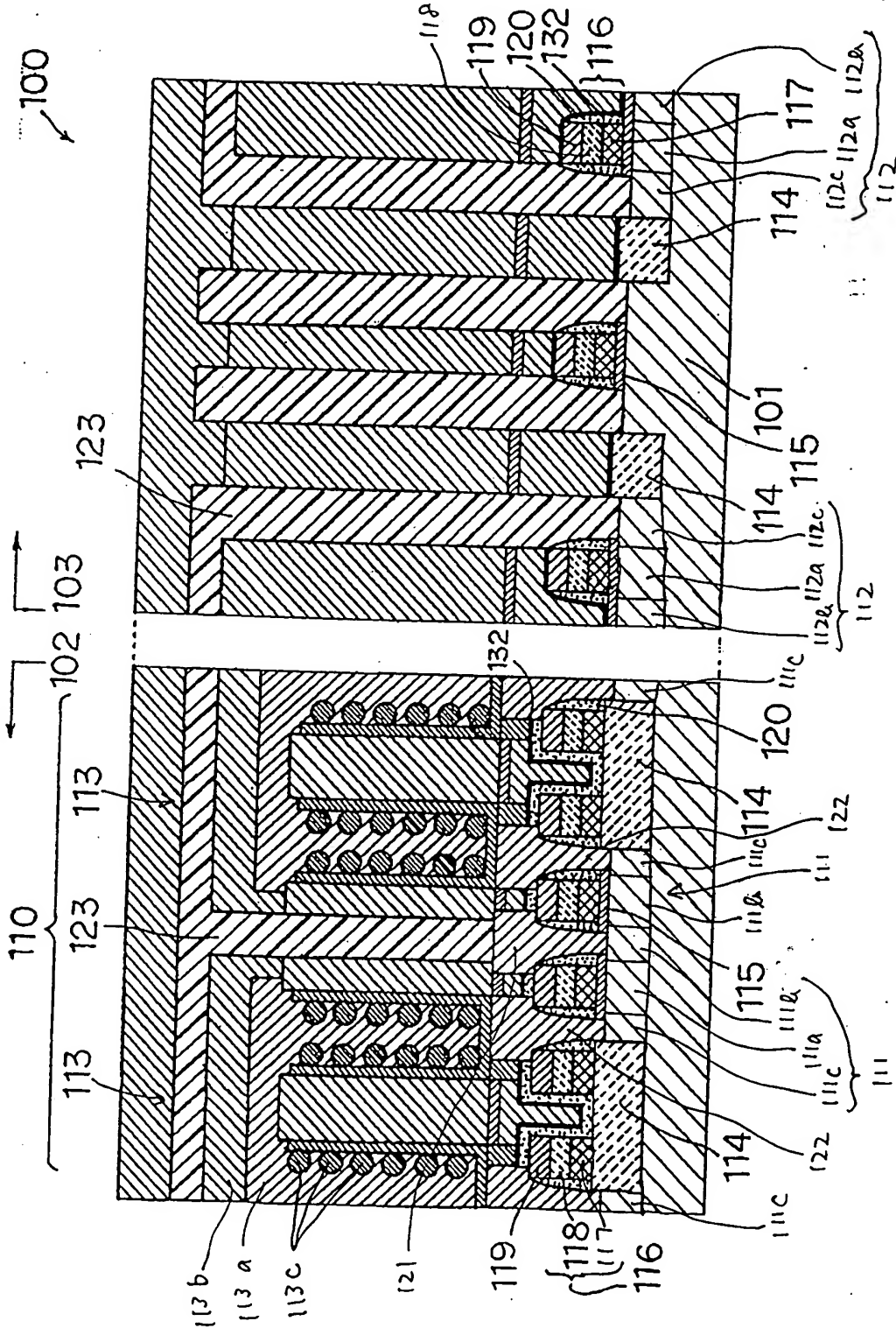


FIG. 2 SEMICONDUCTOR DEVICE WITH HIGH-  
AND LOW-DENSITY REGIONS OF  
TRANSISTOR ELEMENTS ON SINGLE  
SEMICONDUCTOR SUBSTRATE, AND  
METHOD OF MANUFACTURING SUCH  
SEMICONDUCTOR DEVICE

Inventor(s): Toshiyuki HIROTA, et al.

DOCKET NO.: 040373/0300

Fig. 2 (Prior Art)

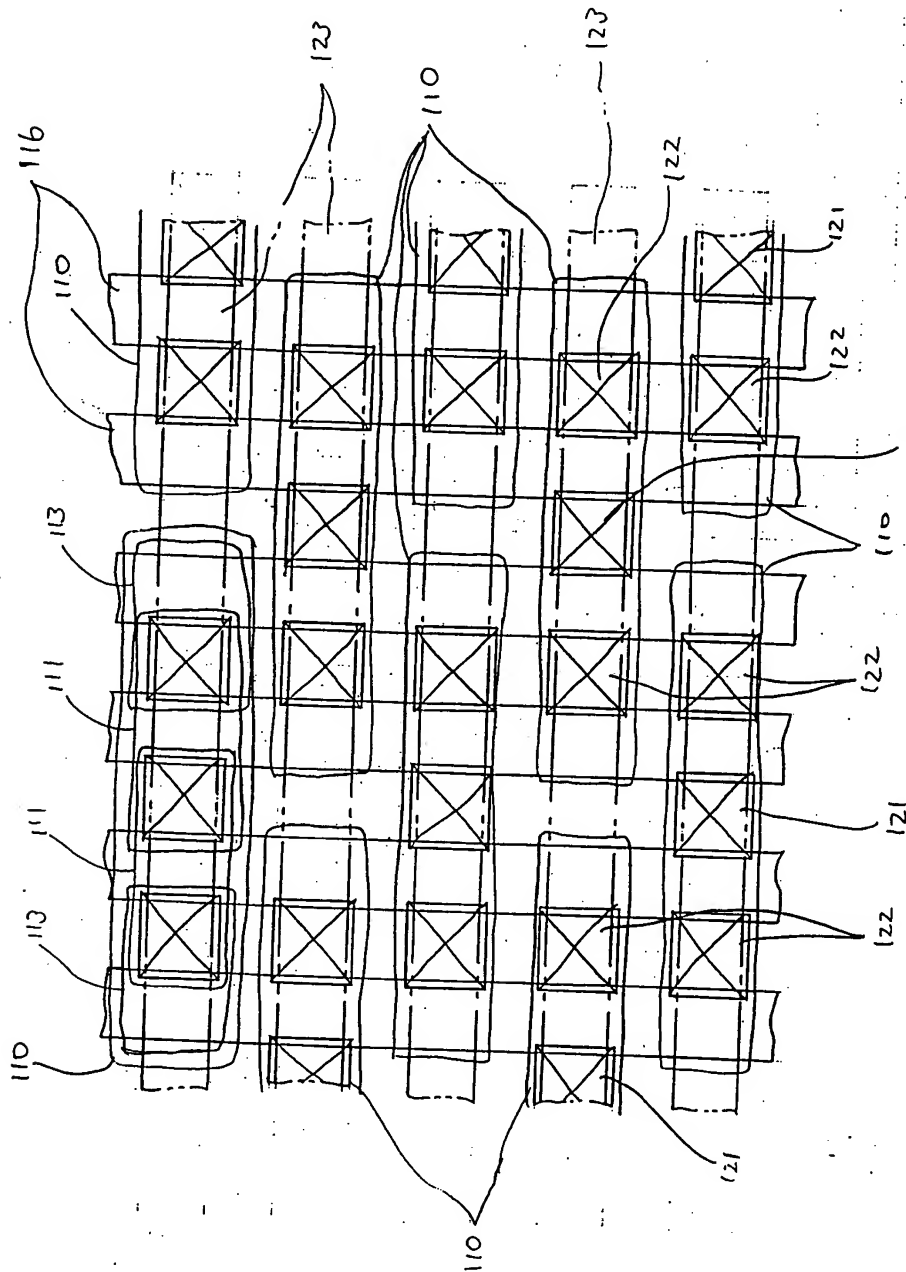


Fig. 3 (Prior Art)

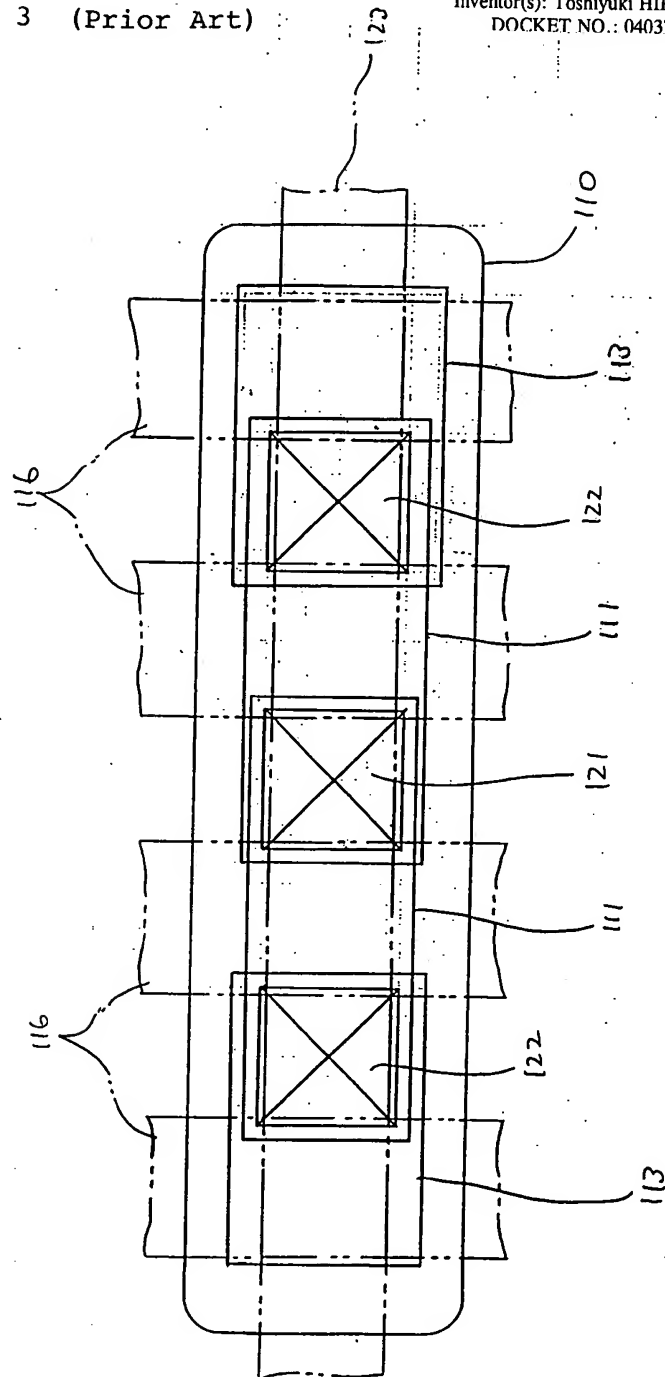
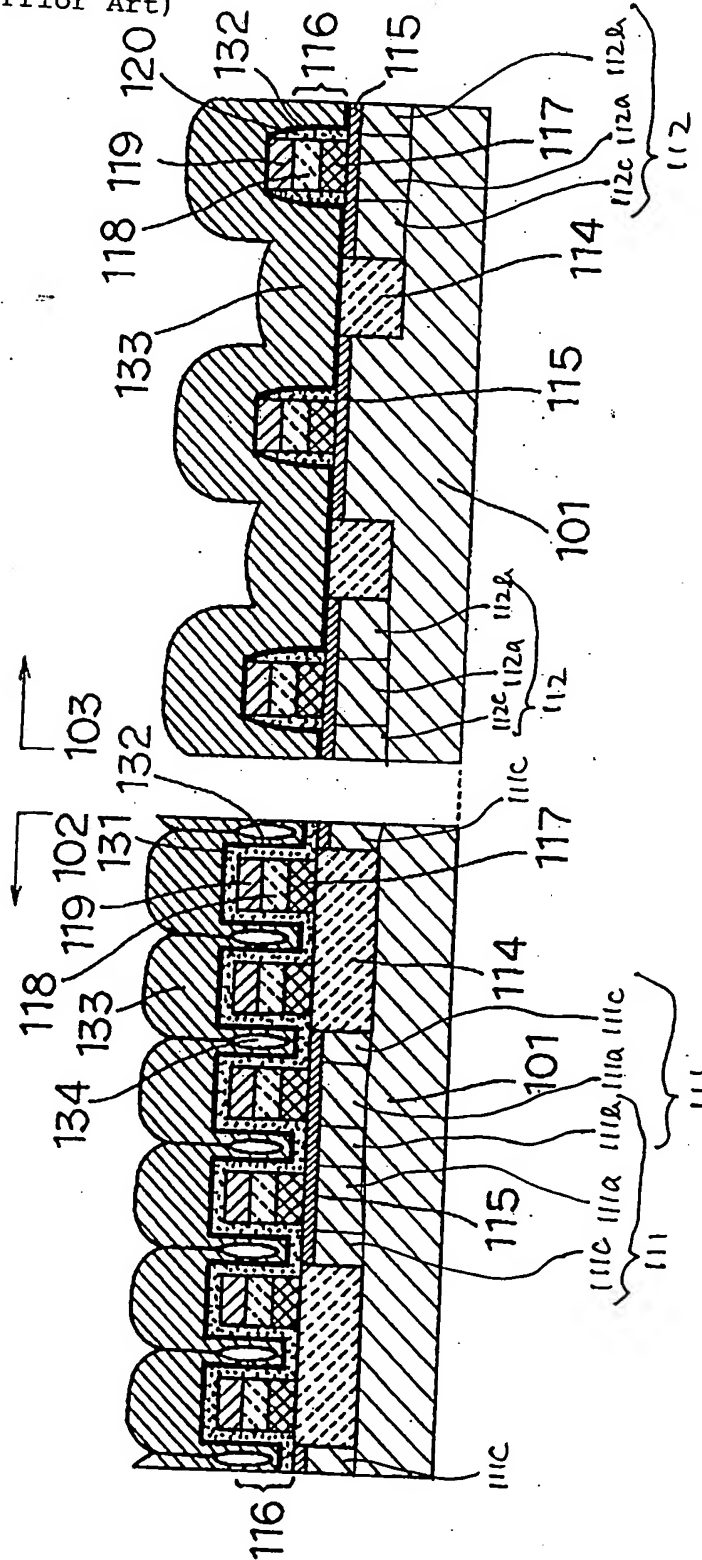


Fig. 4 (Prior Art)



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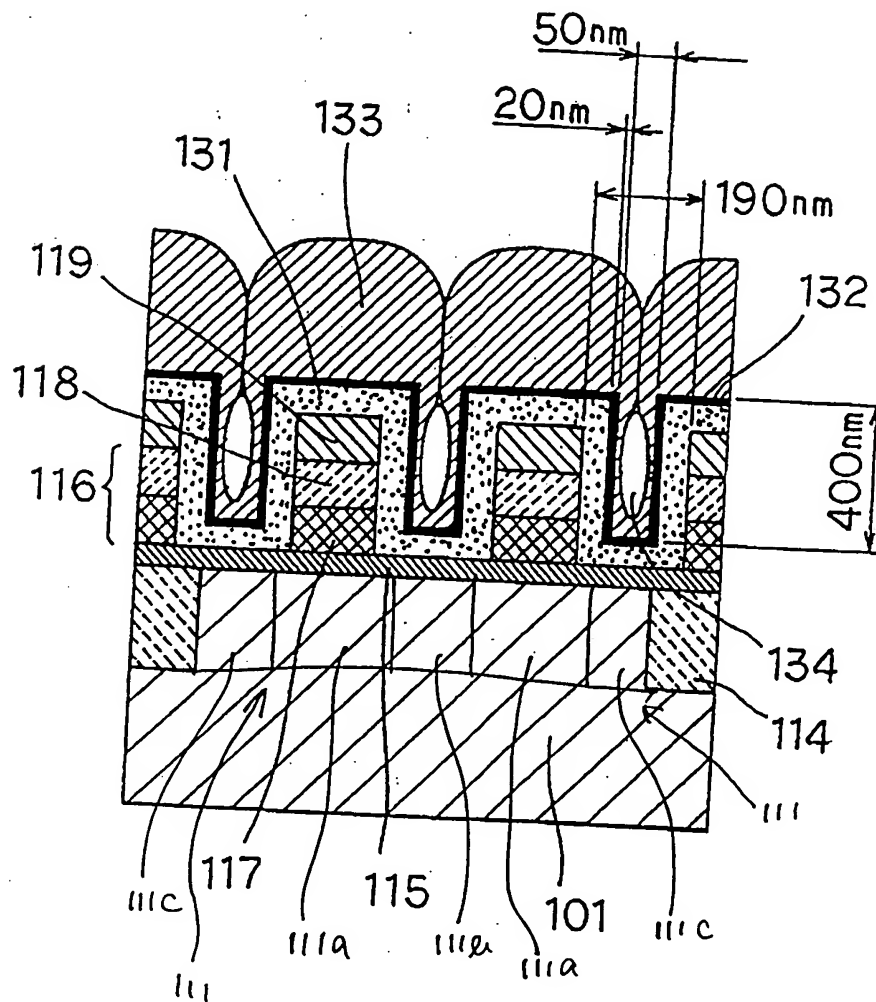
[illegible]

Fig. 6 (Prior Art)

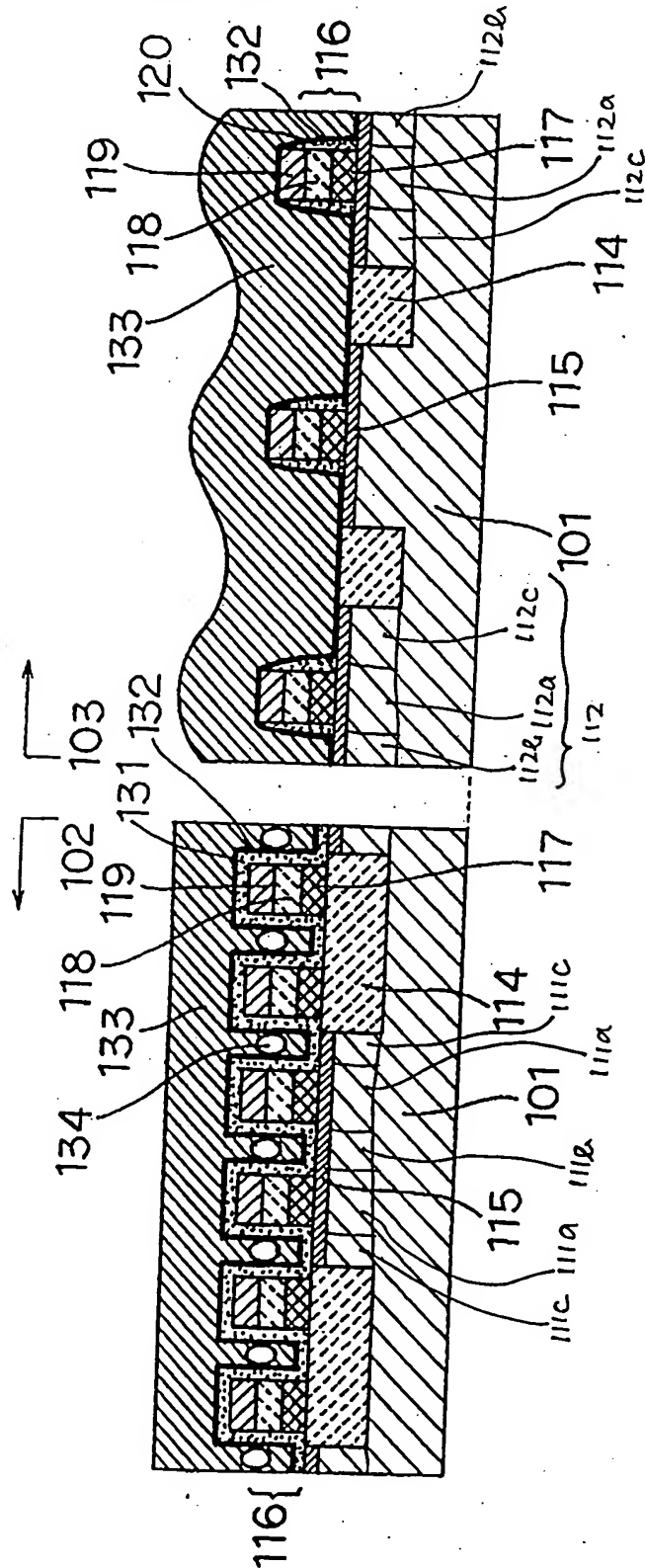
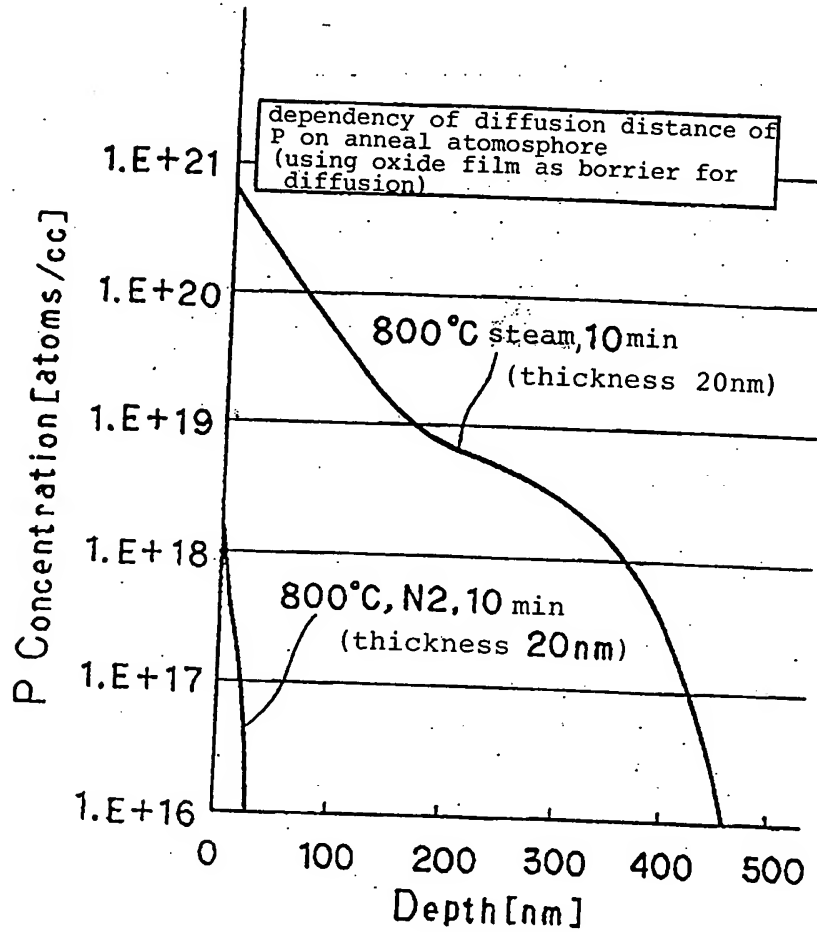


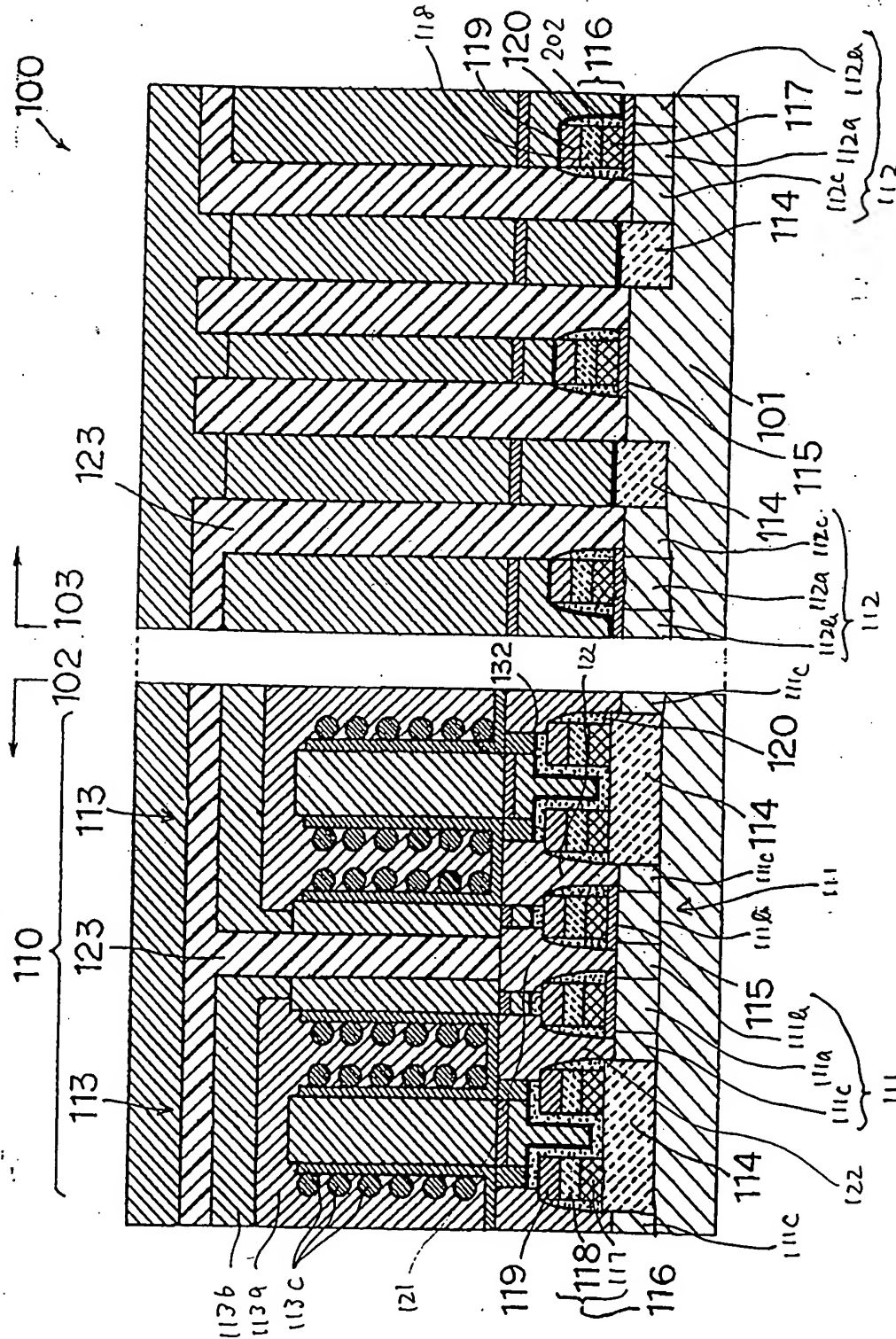
Fig. 7 (Prior Art)



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Fig. 8

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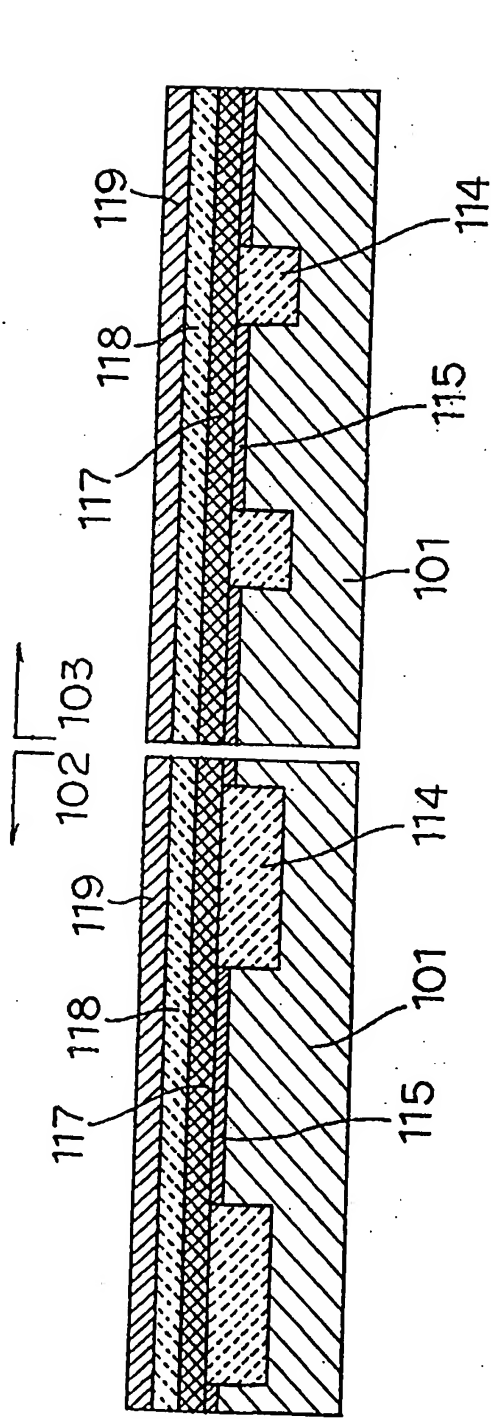


Fig. 9A

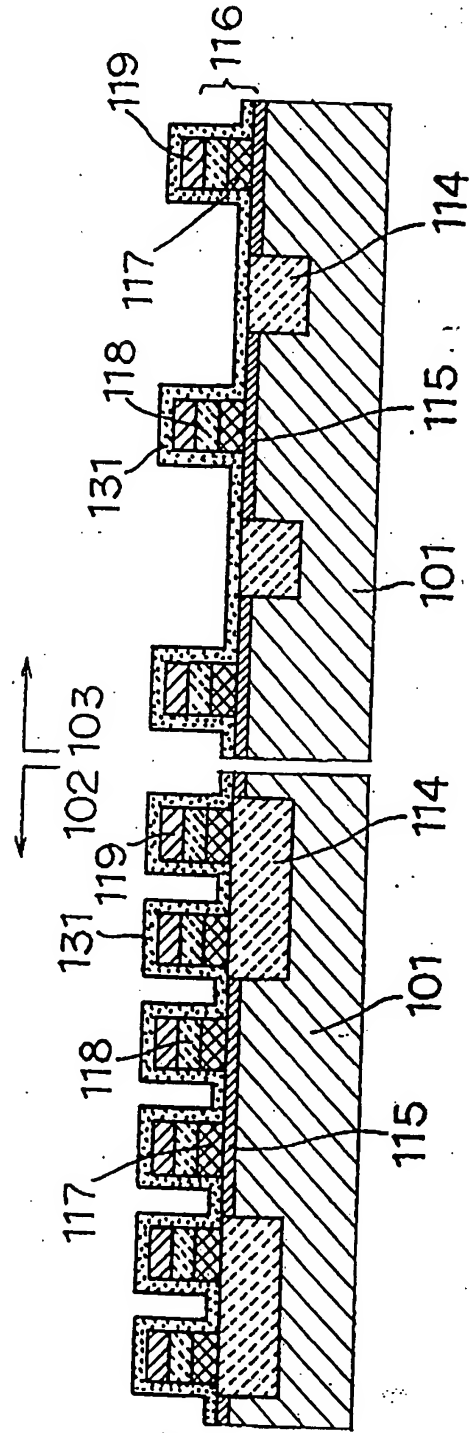
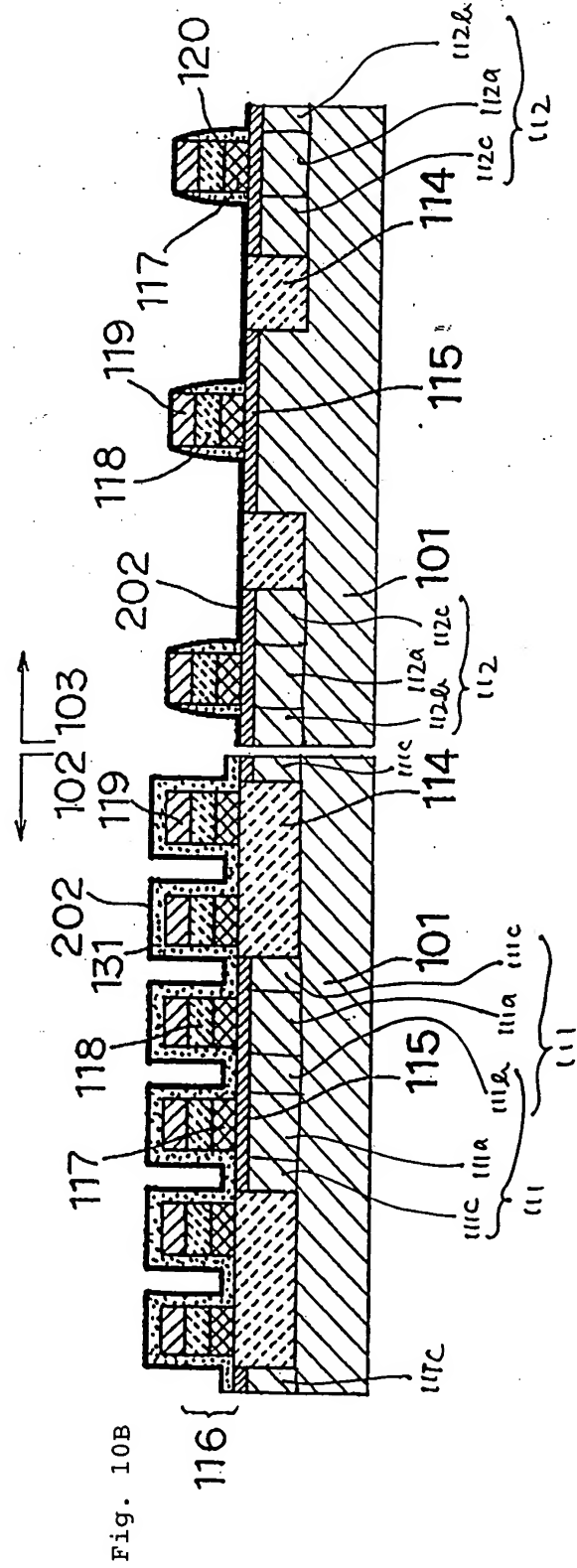
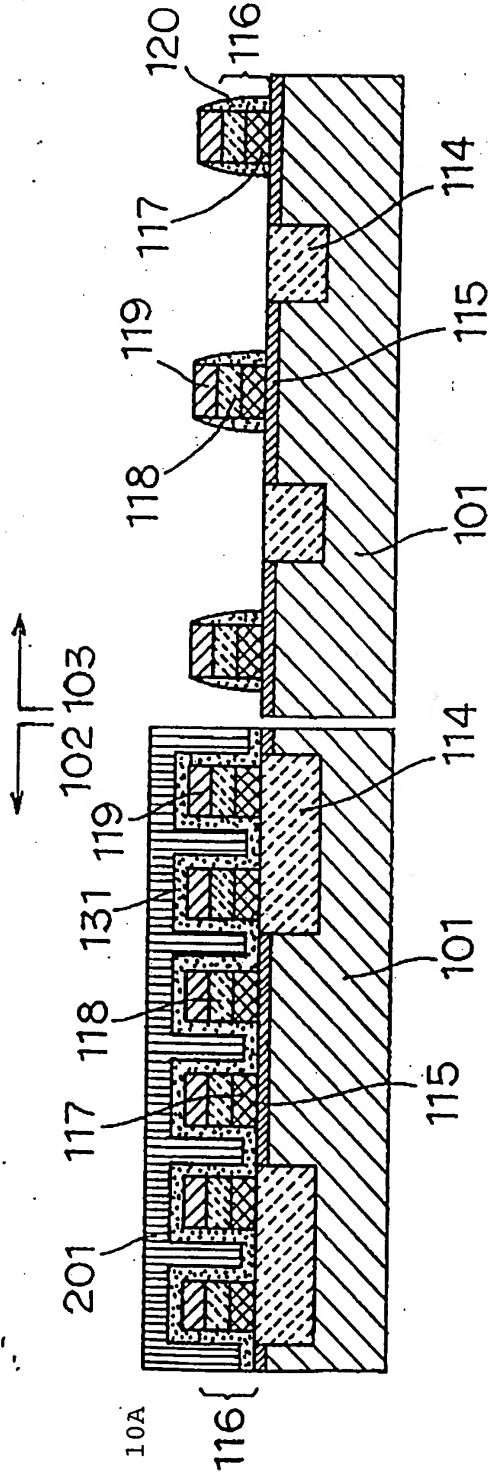
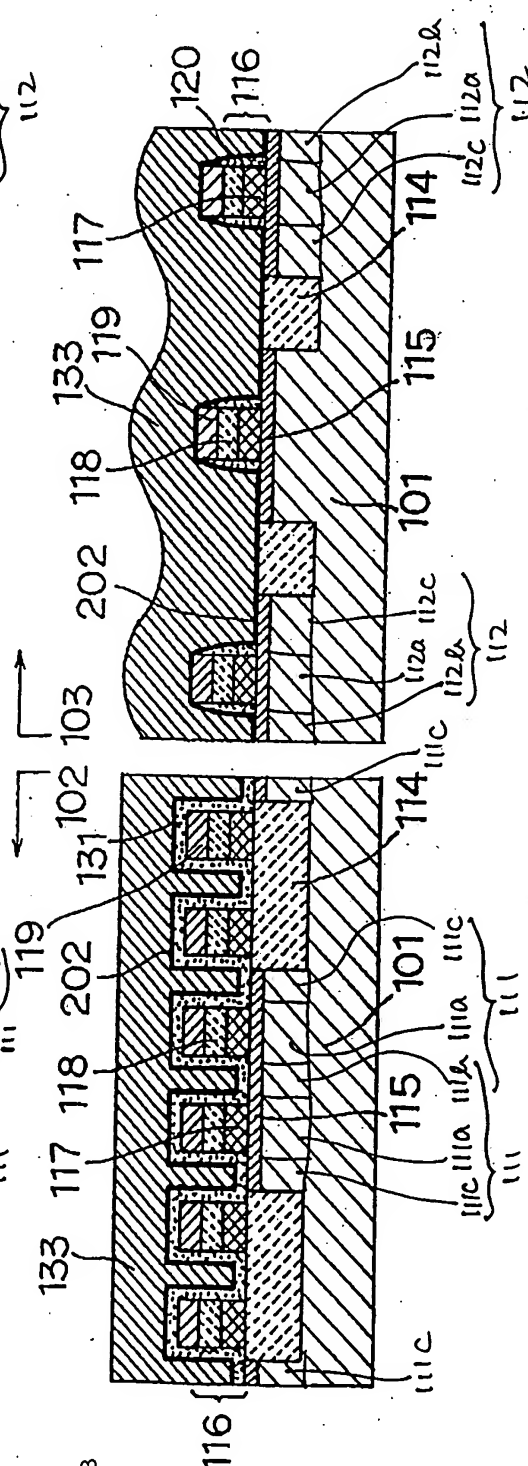
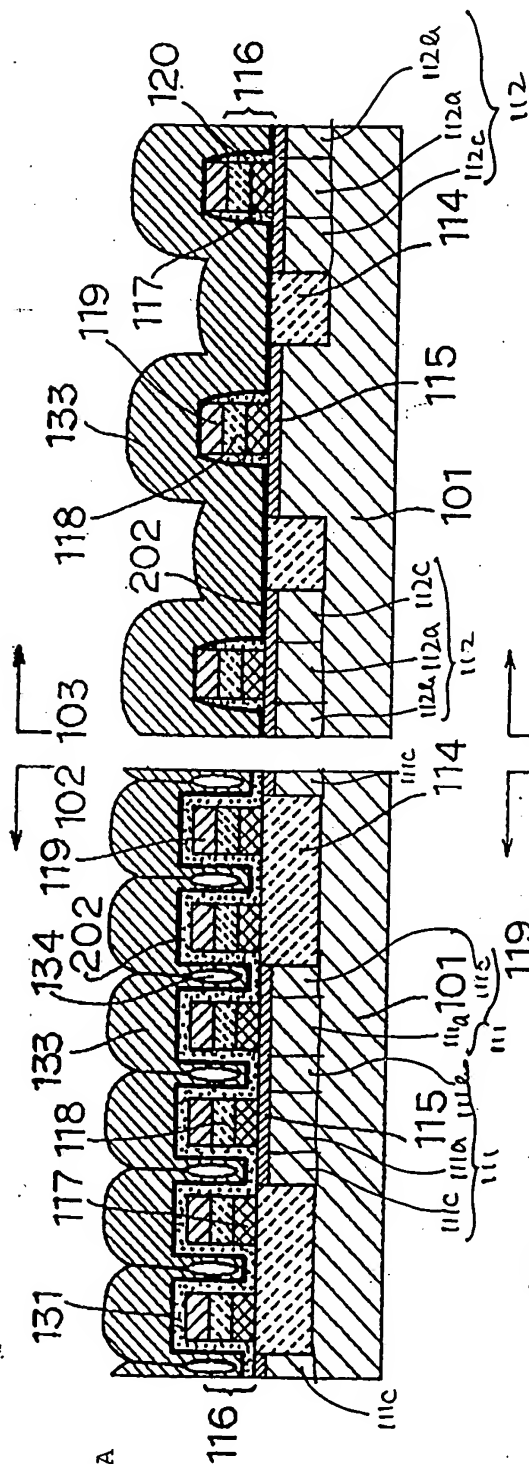


Fig. 9B

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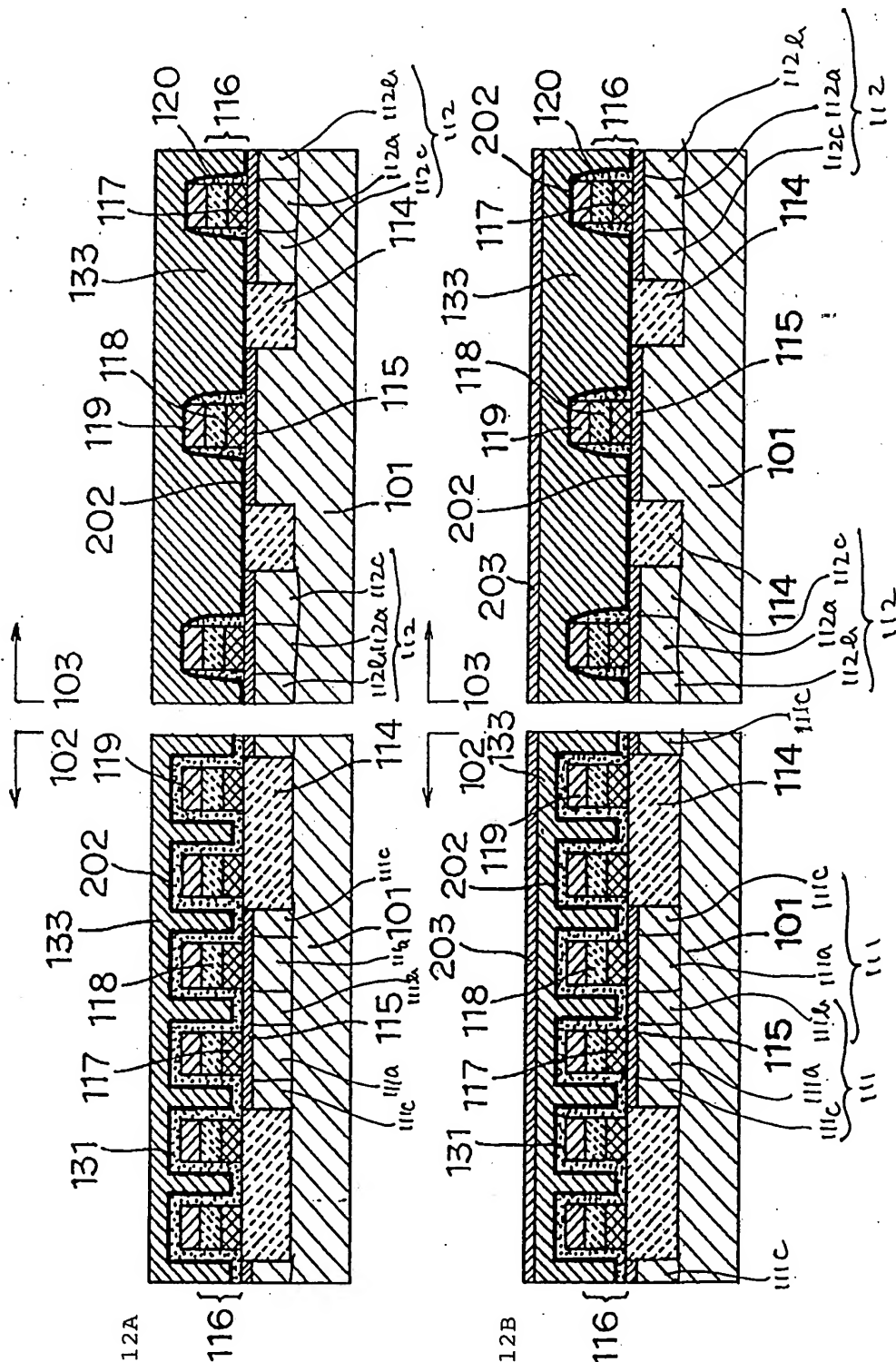


Fig. 12A

Fig. 12B

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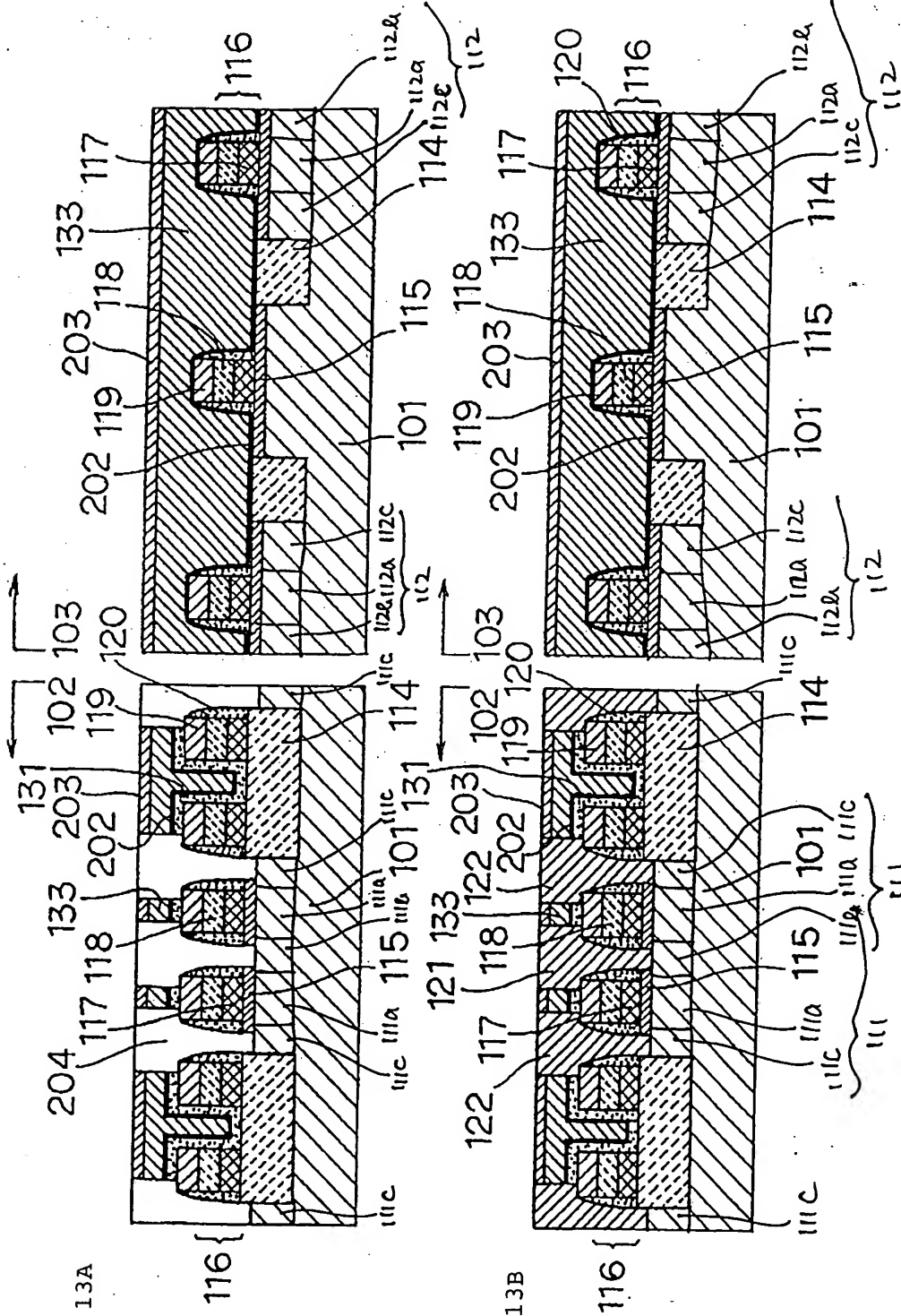


Fig. 13A

Fig. 13B

Fig. 14

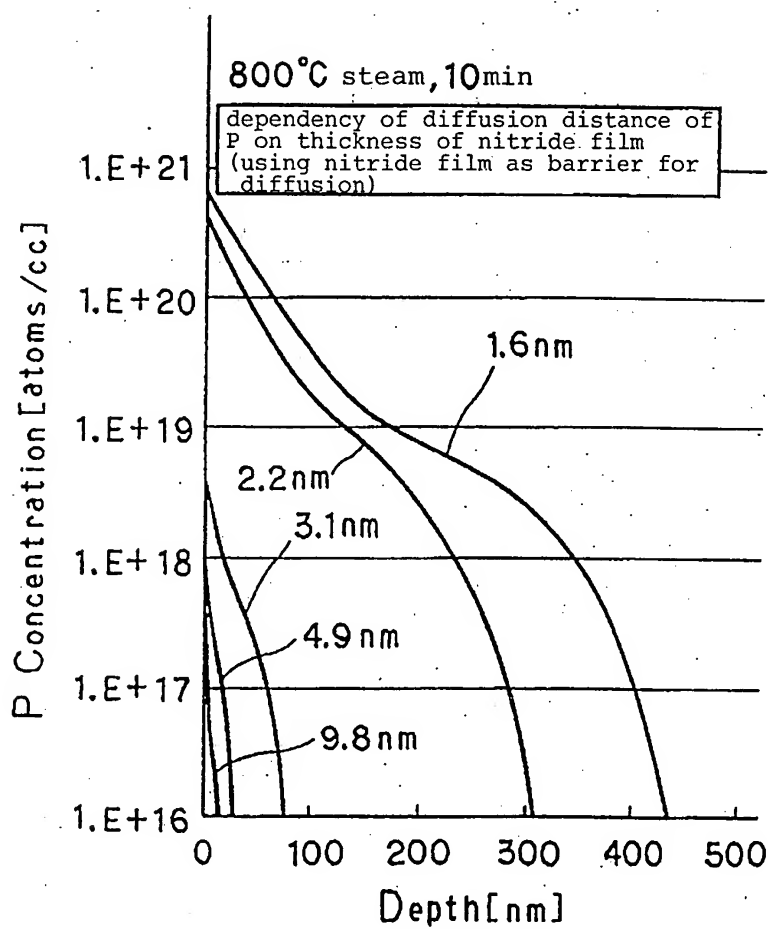


Fig. 15

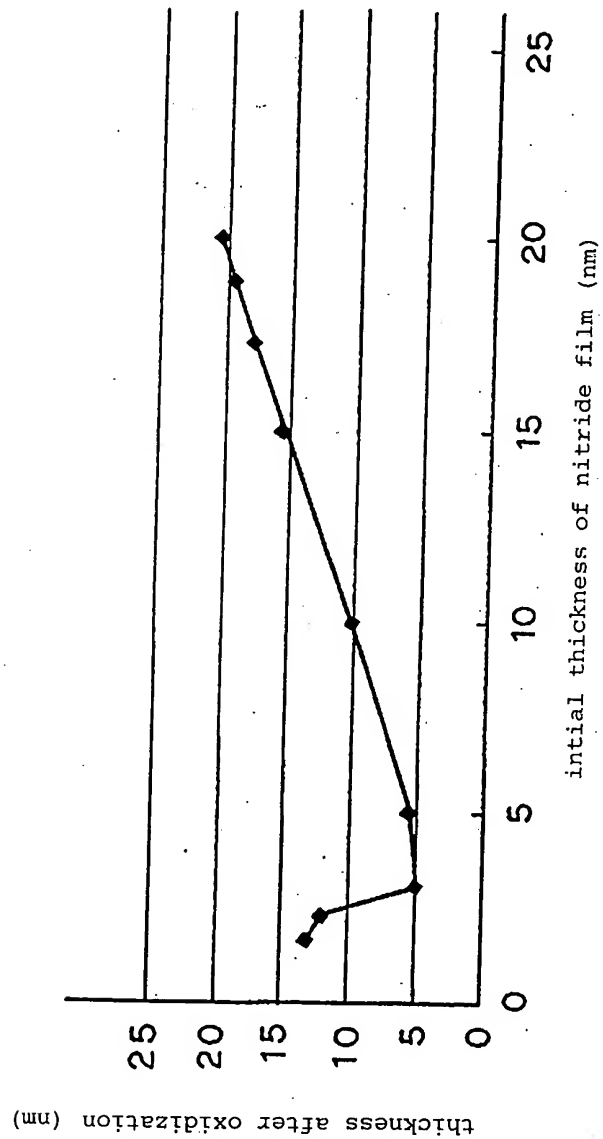


Fig. 16

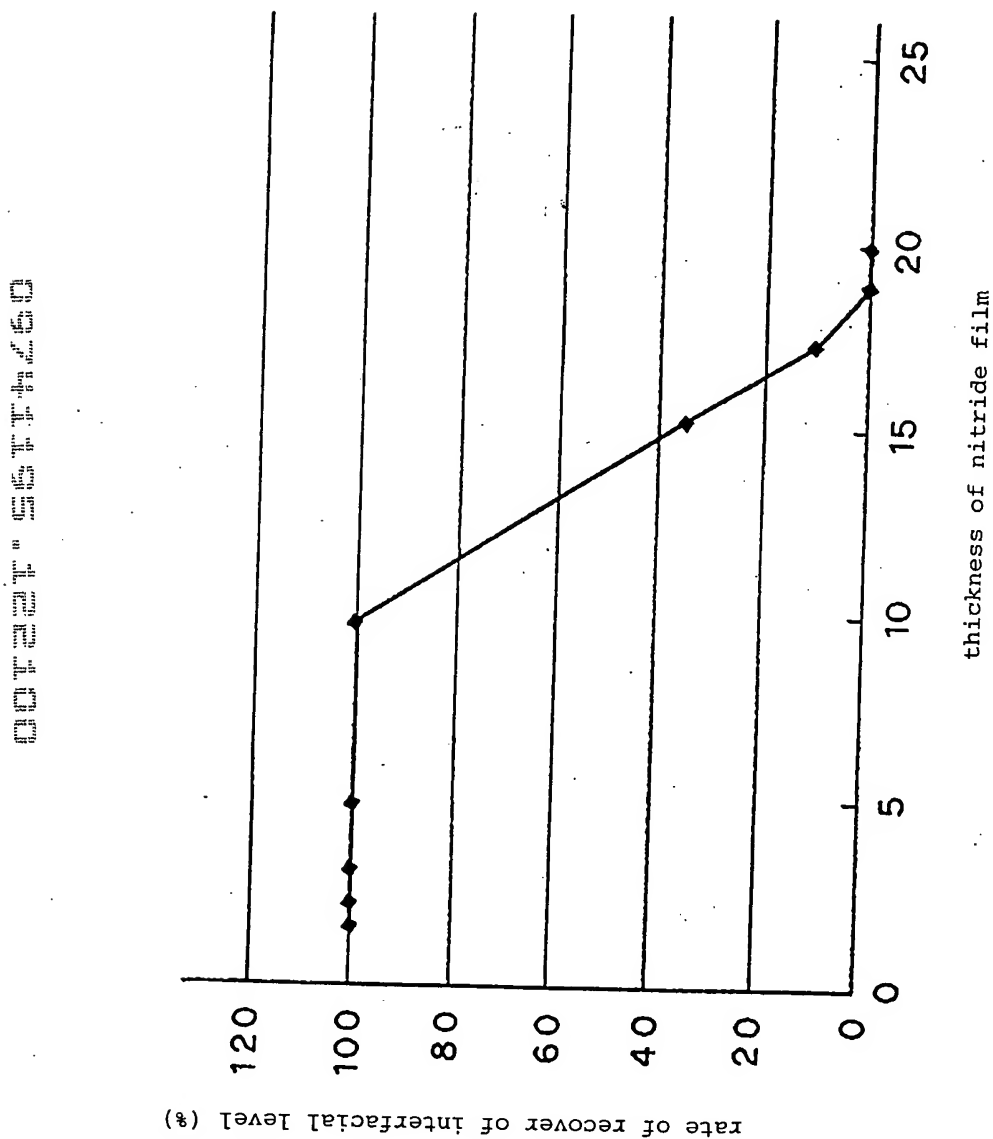
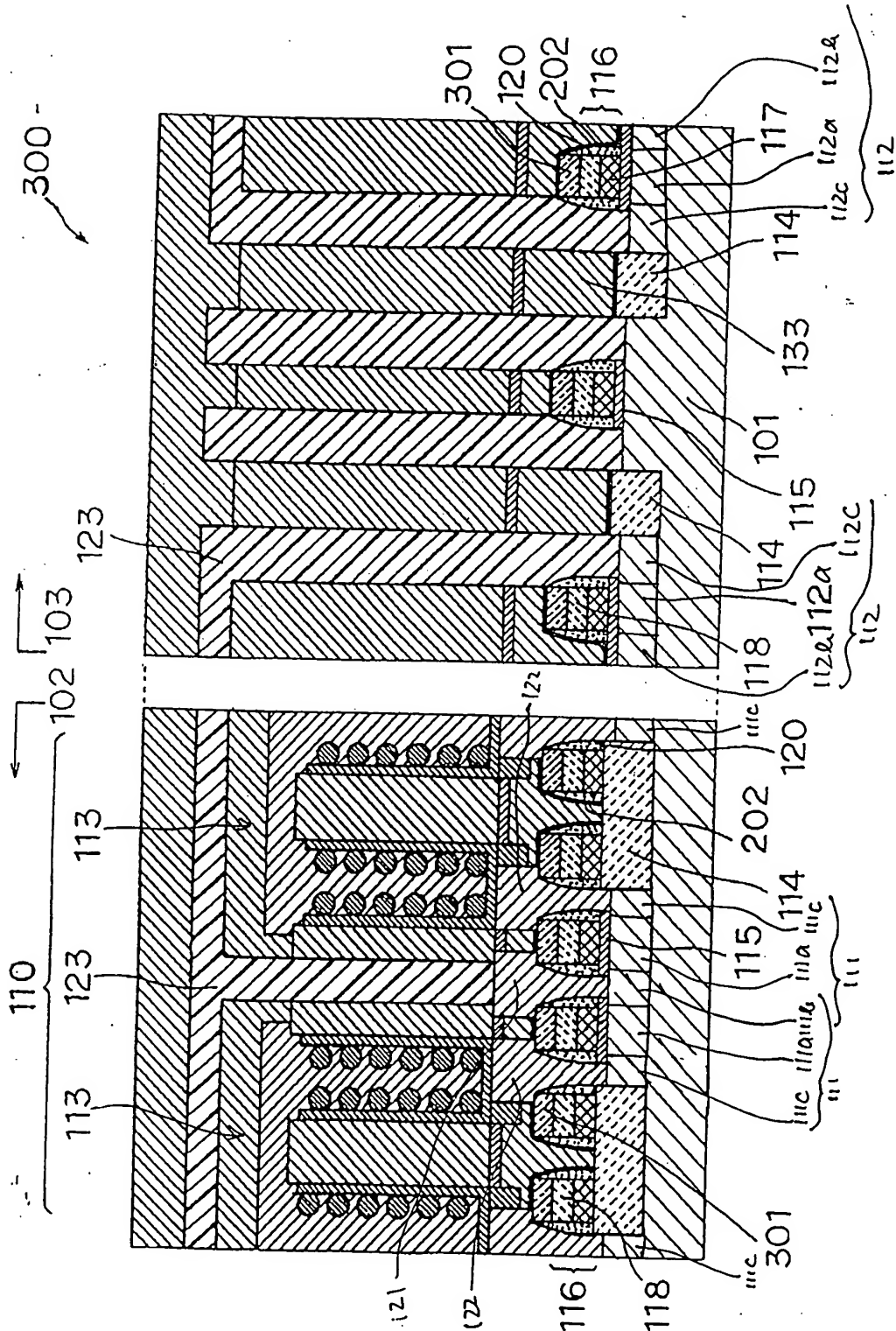




Fig. 17



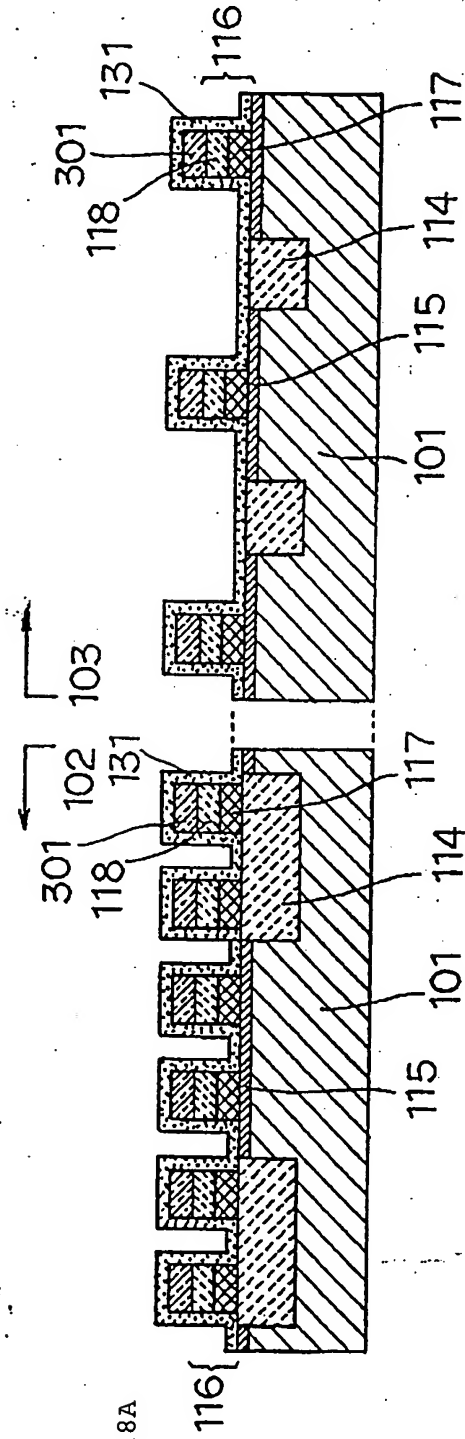


Fig. 18A

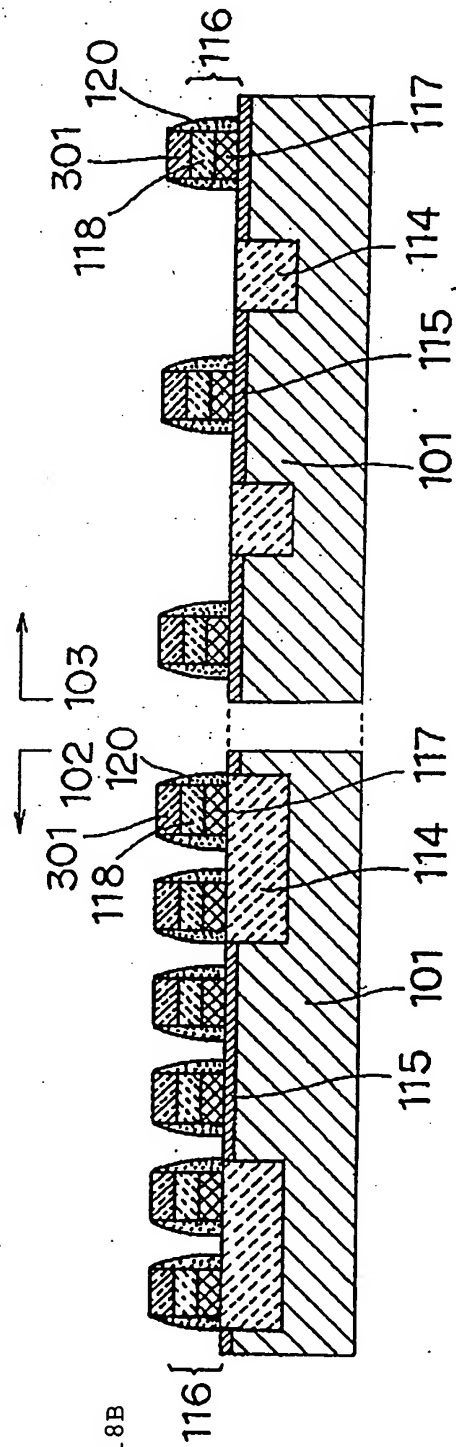


Fig. 18B

Fig. 19B

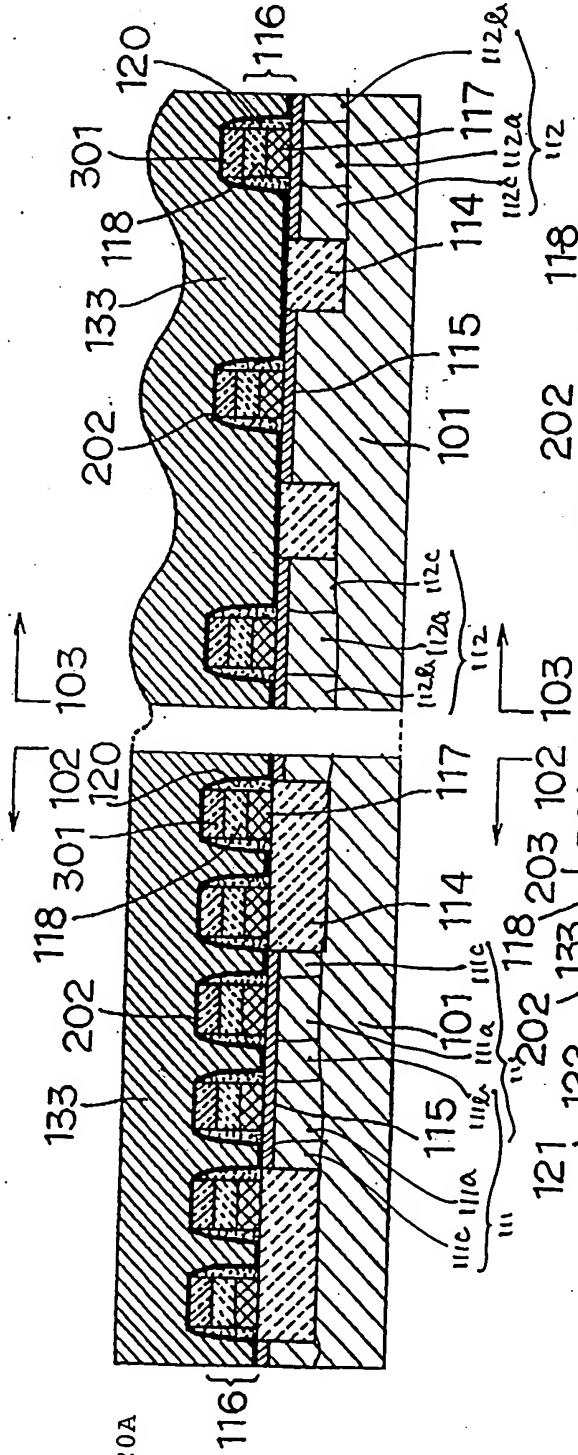


Fig. 20A

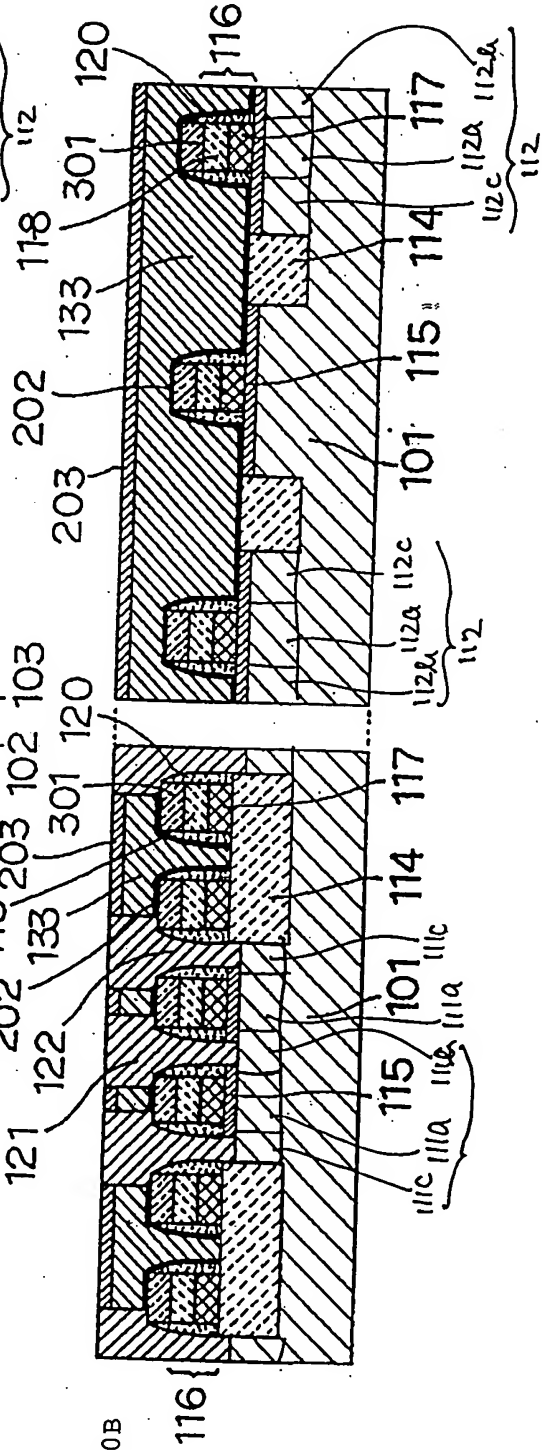
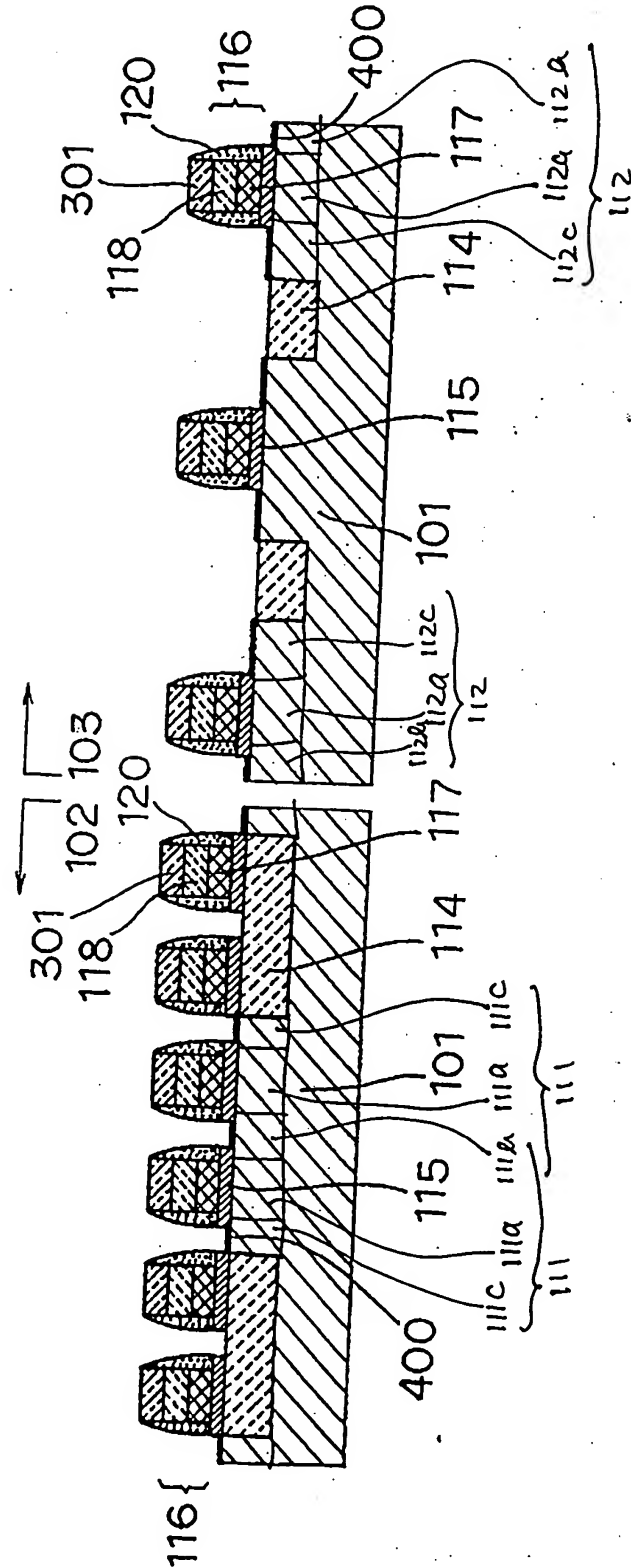


Fig. 20B

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Fig. 22



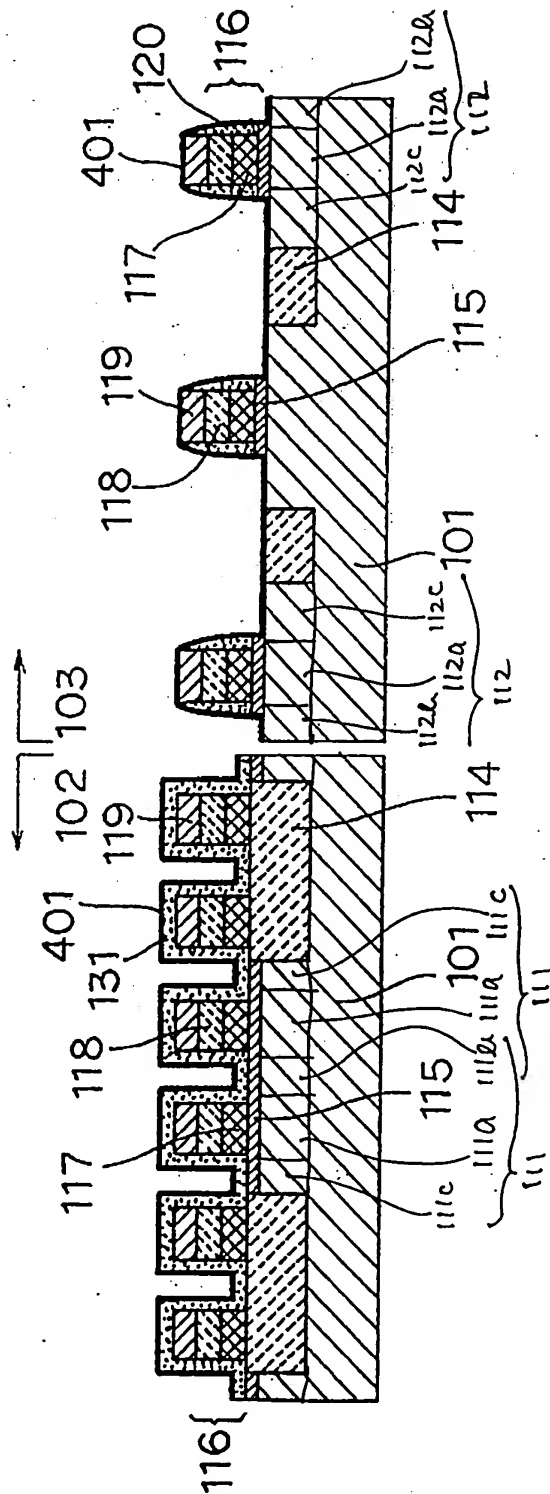
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Fig. 24

